



**DNLS350** 

### LOW VCE(SAT) NPN TRANSISTOR IN SOT223

#### **Features**

- BV<sub>CEO</sub> > 60V
- I<sub>C</sub> = 3.0A High Continuous Current
- Extremely Low Equivalent On-Resistance;  $R_{CE(SAT)}$  62m $\Omega$  at 2A
- Complementary PNP Type: DPLS350E
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

### **Mechanical Data**

- Case: SOT223
- Case Material: Molded Plastic, "Green" Molding Compound.
   UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads. Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.112 grams (Approximate)

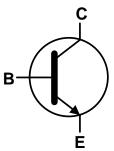
## **Applications**

• Ideal for Medium Power Switching or Amplification Applications

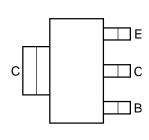




Top View



Device Symbol



Top View Pin-Out

### Ordering Information (Note 4)

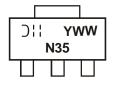
Product	Compliance	Marking	Reel Size (inches)	Tape Width (mm)	Quantity per Reel
DNLS350E-13	AEC-Q101	N35	13	12	2,500

Notes:

- 1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.
- 2. See http://www.diodes.com/quality/lead\_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

## **Marking Information**

**SOT223** 



N35 = Product Type Marking Code YWW = Date Code Marking Y = Last Digit of Year (ex: 15 = 2015) WW = Week Code (01 - 52)



# **Absolute Maximum Ratings** ( $@T_A = +25^{\circ}C$ , unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V <sub>CBO</sub>	60	V
Collector-Emitter Voltage	V <sub>CEO</sub>	50	V
Emitter-Base Voltage	V <sub>EBO</sub>	6	V
Continuous Collector Current	Ic	3	Α
Peak Pulse Collector Current	Ісм	5	Α
Peak Pulse Base Current	I <sub>BM</sub>	1	Α

## Thermal Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
	(Note 5)		3		
Power Dissipation	(Note 6)	P <sub>D</sub>	2	W	
	(Note 7)		1		
	(Note 5)		41.7		
Thermal Resistance, Junction to Ambient	(Note 6)	R <sub>0JA</sub>	62.5	°C/W	
	(Note 7)		125	1	
Thermal Resistance, Junction to Leads (Note 8)		R <sub>0JL</sub>	15	°C/W	
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C		

## ESD Ratings (Note 9)

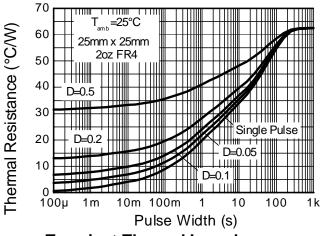
Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge – Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge – Machine Model	ESD MM	400	V	С

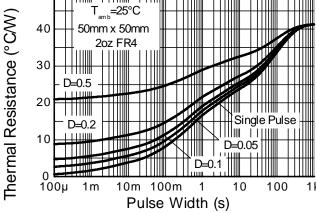
Notes:

- For a device mounted with the collector lead on 50mm x 50mm 2oz copper that is on a single-sided 1.6mm FR4 PCB; device is measured under still air conditions whilst operating in a steady-state.
   Same as Note (5), except mounted on 25mm x 25mm 2oz copper.
   Same as Note (5), except mounted on minimum recommended pad (MRP) layout.
   Thermal resistance from junction to solder-point (at the end of the collector lead).
   Refer to JEDEC specification JESD22-A114 and JESD22-A115.



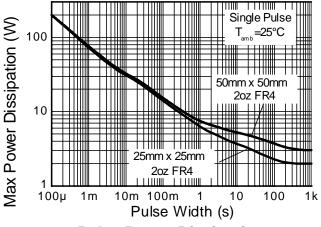
## **Thermal Characteristics and Derating Information**

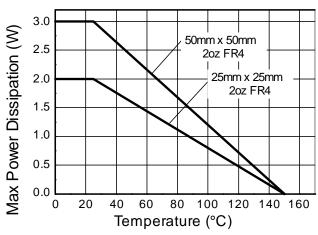




**Transient Thermal Impedance** 







**Pulse Power Dissipation** 

**Derating Curve** 



# **Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Conditions
OFF CHARACTERISTICS						
Collector-Base Breakdown Voltage	$BV_{CBO}$	50	_	_	V	$I_{C} = 100 \mu A$
Collector-Emitter Breakdown Voltage (Note 10)	BV <sub>CEO</sub>	50	_	_	V	I <sub>C</sub> = 10mA
Emitter-Base Breakdown Voltage	BV <sub>EBO</sub>	6	_	_	V	$I_{E} = 100 \mu A$
Collector-Base Cutoff Current	1		_	100	nA	$V_{CB} = 50V, I_{E} = 0$
Collector-base Cuton Current	I <sub>CBO</sub>		_	50	μΑ	$V_{CB} = 50V, I_{E} = 0, T_{A} = +150^{\circ}C$
Emitter-Base Cutoff Current	I <sub>EBO</sub>	_	_	100	nA	$V_{EB} = 5V, I_{C} = 0$
ON CHARACTERISTICS (Note 10)						
		200		_		$V_{CE} = 2V, I_{C} = 0.5A$
DC Current Gain	h <sub>FE</sub>	200	_	_	_	$V_{CE} = 2V$ , $I_C = 1A$
		100	_	_		$V_{CE} = 2V$ , $I_C = 2A$
			_	90	1	$I_C = 0.5A, I_B = 50mA$
Collector-Emitter Saturation Voltage	V <sub>CE(SAT)</sub>		_	170		$I_C = 1A, I_B = 50mA$
			_	290		$I_C = 2A$ , $I_B = 200mA$
Equivalent On-Resistance	R <sub>CE(SAT)</sub>		62	145	mΩ	I <sub>C</sub> = 2A, I <sub>B</sub> = 200mA
Base-Emitter Saturation Voltage	V <sub>BE(SAT)</sub>		_	1.2	V	$I_C = 2A$ , $I_B = 200mA$
Base-Emitter Turn-On Voltage	V <sub>BE(ON)</sub>		_	1.1	V	$V_{CE} = 2V$ , $I_C = 1A$
SMALL SIGNAL CHARACTERISTICS						
Transition Frequency	f⊤	100	_	_	MHz	$V_{CE} = 5V, I_{C} = 100mA,$ f = 100MHz
Output Capacitance	$C_{ m obo}$	_	_	30	pF	V <sub>CB</sub> = 10V, f = 1MHz

Note: 10. Measured under pulsed conditions. Pulse width  $\leq$  300 $\mu$ s. Duty cycle  $\leq$  2%.



## Typical Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

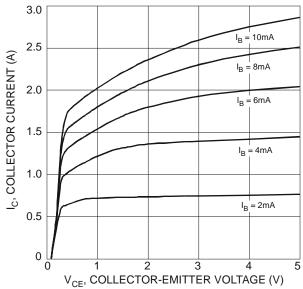
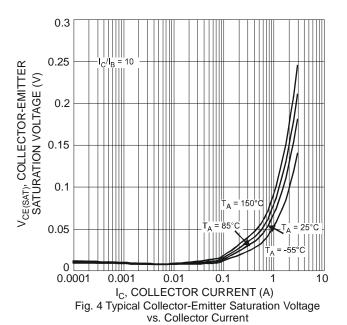


Fig. 2 Typical Collector Current vs. Collector-Emitter Voltage



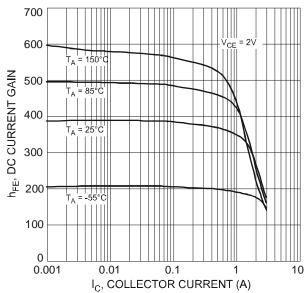


Fig. 3 Typical DC Current Gain vs. Collector Current

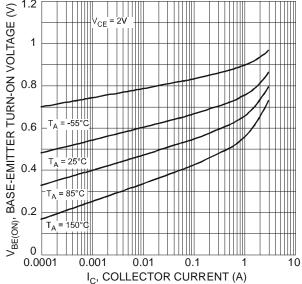
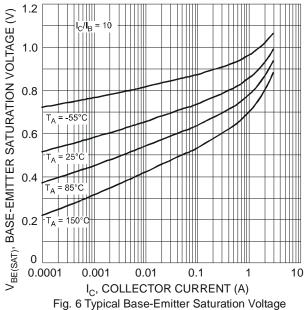


Fig. 5 Typical Base-Emitter Turn-On Voltage vs. Collector Current



## Typical Electrical Characteristics (Continued) (@T<sub>A</sub> = +25°C, unless otherwise specified.)



vs. Collector Current

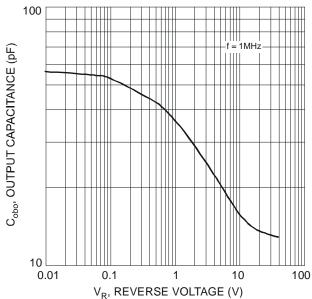
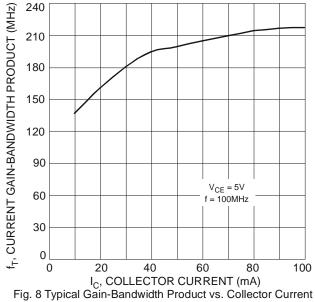


Fig. 7 Typical Output Capacitance Characteristics

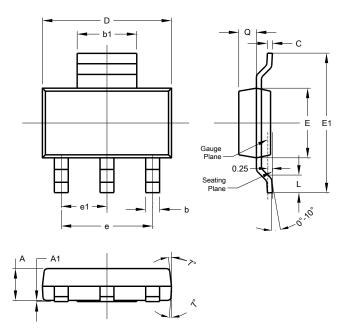




# **Package Outline Dimensions**

Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.

#### **SOT223**

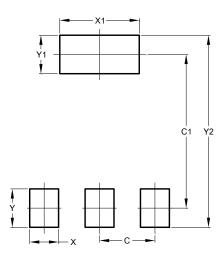


SOT223					
Dim	Min	Max	Тур		
Α	1.55	1.65	1.60		
A1	0.010	0.15	0.05		
b	0.60	0.80	0.70		
b1	2.90	3.10	3.00		
С	0.20	0.30	0.25		
D	6.45	6.55	6.50		
Е	3.45	3.55	3.50		
E1	6.90	7.10	7.00		
е	-	-	4.60		
e1	-	-	2.30		
L	0.85	1.05	0.95		
Q	0.84	0.94	0.89		
All Dimensions in mm					

# Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.

### **SOT223**



Dimensions	Value (in mm)
C	2.30
C1	6.40
Х	1.20
X1	3.30
Y	1.60
Y1	1.60
Y2	8.00



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